

Engineering/Process Change Notice

ECN/PCN No.: 4476

For Manufacturer					
Product Description: Ceramic SMD Crystal Oscillator	Abracon Part Numb EP16E7 Series	er / Part Series:	□ Documentation only⋈ ECN⋈ EOL	⊠ Series □ Part Number □	
Affected Revision: Rev. G 12/11/2012	New Revision:	DL	Application:	☐ Safety ☑ Non-Safety	
Prior to Change: ACTIVE					
After Change: EOL					
Cause/Reason for Change: Discontinuation of manufacturing capabilit	ty				
	Chan	ge Plan			
Effective Date: 11/15/2022	Additional Remarks: N/A				
Change Declaration: N/A					
Issued Date: 11/15/22	Issued By:		Issued Department:		
Approval:	Approval:		Approval:		
	For Abrac	on EOL only			
		Alternate Part Number / Part Series: ASEDV, ASE3, AP3S			
Additional Approval:	Additional Approval	:	Additional Approval:		
Customer Approval (If Applicable)					
Qualification Status: $ \square \ \text{Approved} \ \square \ \text{Not accepted} $ Not accepted $ \text{Note: It is considered approved if there is no feedback from the customer 1 month after ECN/PCN is released.} $					
Customer Part Number:		Customer Project:			
Company Name:	Company Representative:		Representative Signature:		
Customer Remarks:					















REGULATORY COMPLIANCE











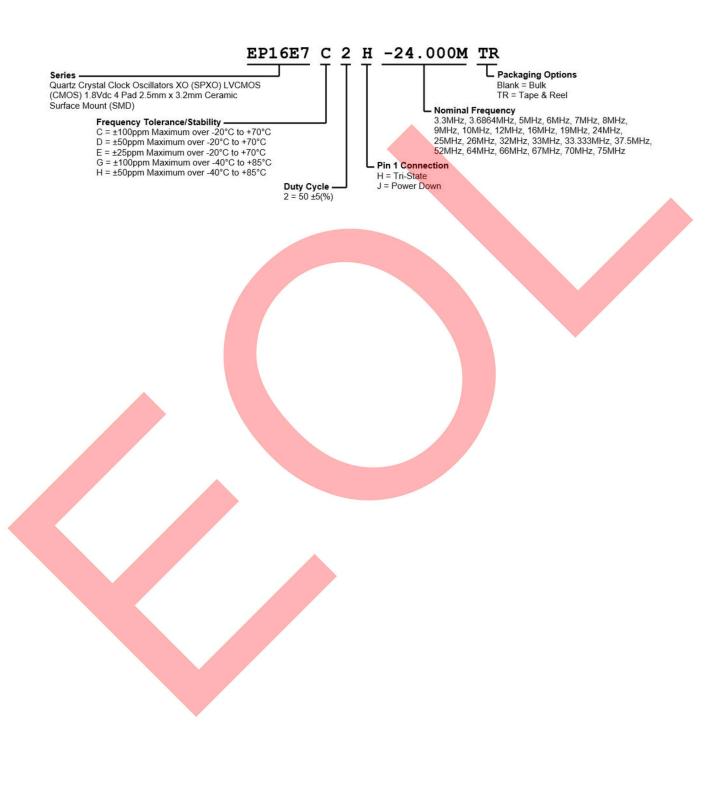
ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 1.8Vdc 4 pad 2.5mm x 3.2mm Ceramic Surface Mount (SMD)

ELECTRICAL SPECIFICAT	TIONS		
Nominal Frequency	3.3MHz to 75MHz		
Frequency Tolerance/Stability	Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, 260°C Reflow, Shock, and Vibration ±100ppm Maximum over -20°C to +70°C ±50ppm Maximum over -20°C to +70°C ±25ppm Maximum over -20°C to +70°C ±100ppm Maximum over -40°C to +85°C ±50ppm Maximum over -40°C to +85°C		
Aging at 25°C	±5ppm/year Maximum		
Supply Voltage	1.8Vdc ±5%		
Input Current	8mA Maximum o <mark>ver Nomin</mark> al Frequency of 3.3MHz to <mark>25MHz</mark> 9mA Maximum <mark>over No</mark> minal Frequency of 25.000001MHz to 50MHz 12mA Maximu <mark>m over Nominal Frequency of 50.000001MHz to 75MHz</mark>		
Output Voltage Logic High (V _{он})	IOH = -8mA 90% of Vdd M <mark>inimu</mark> m		
Output Voltage Logic Low (V _{OL})	IOL = +8mA 10% of Vdd M <mark>aximu</mark> m		
Rise/Fall Time	Measured at 2 <mark>0% to 8</mark> 0% of waveform 6nSec Maximu <mark>m over N</mark> ominal Frequency of 3.3MHz to 50MHz 4nSec Maximum over Nominal Frequency of 50.000001MHz to 75MHz		
Duty Cycle	Measured at 50% <mark>of wavefo</mark> rm 50 ±5(%)		
Load Drive Capability	15pF Maximum		
Output Logic Type	CMOS		
Pin 1 Connection	Tri-State Power <mark>Down</mark>		
Pin 1 Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output		
Standby Current	<mark>30µА Ma</mark> ximum (Pin 1 = Ground, Power Down)		
Disable Current	4mA Maximum (Pin 1 = Ground, Tri-State)		
Absolute Clock Jitter	350pSec Maximum over No <mark>minal Fre</mark> quency of 3.3MHz to 24.999999MHz 200pSec Maximum over Nominal Frequency of 25MHz to 75MHz		
Start Up Time	10mSec Maximum		
Storage Temperature Range	-55°C to 125°C		

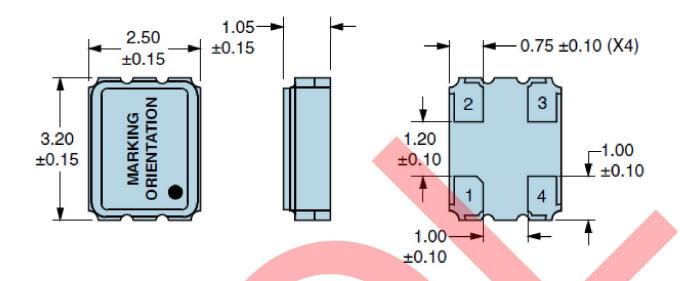


PART NUMBERING GUIDE

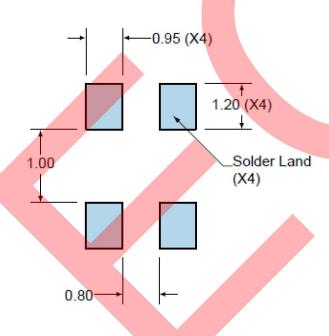




MECHANICAL DIMENSIONS



SUGGESTED SOLDER PAD LAYOUT



1	Power Down Or Tri-State
2	Ground
3	Output
4	Supply Voltage

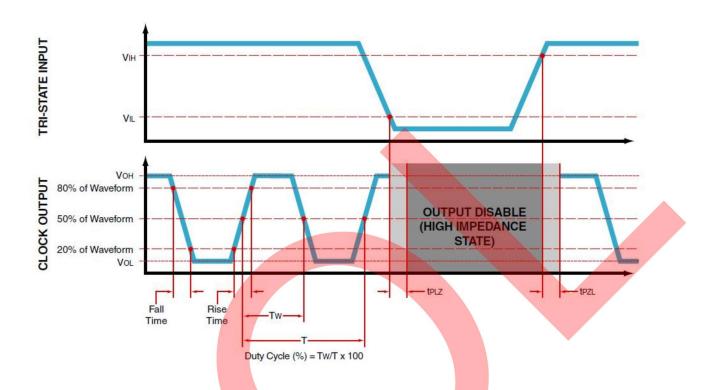
CONNECTION

All Tolerances are ±0.1

All Dimensions in Millimeters

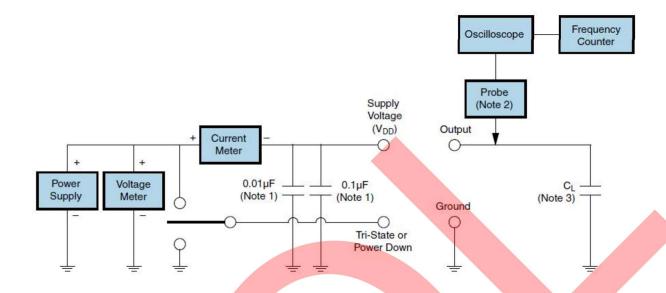


OUTPUT WAVEFORM & TIMING DIAGRAM





TEST CIRCUIT FOR CMOS OUTPUT



Note 1: An external 0.01µF Ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass Capacitor close (less Than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low input capacitance (<12pF), 10X Attenuation factor, High impedance (>10Mohms), and High bandwidth (>300MHz) Passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance. See applicable specification sheet for 'Load Drive Capability'.

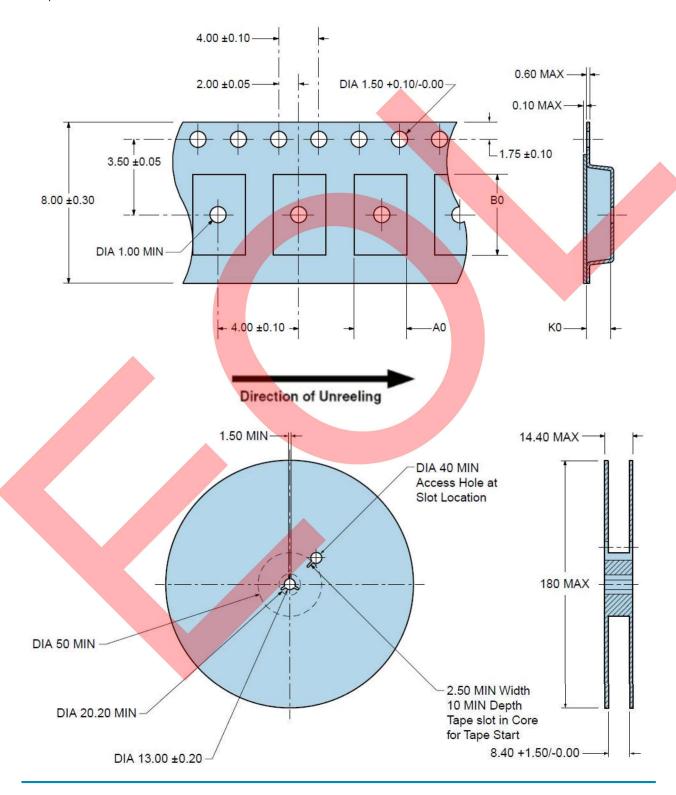


TAPE & REEL DIMENSIONS

Quantity per Reel: 1,000 Units

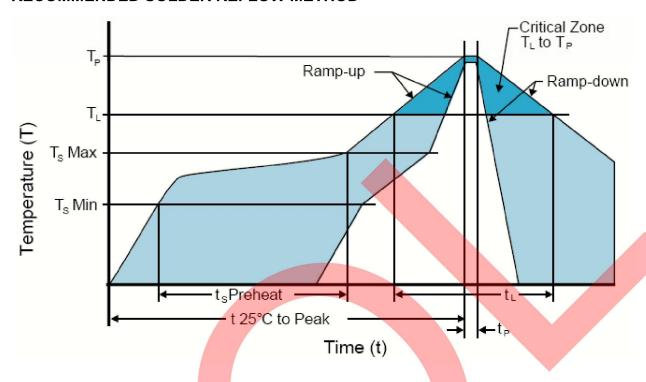
All Dimensions in Millimeters

Compliant to EIA-481





RECOMMENDED SOLDER REFLOW METHOD



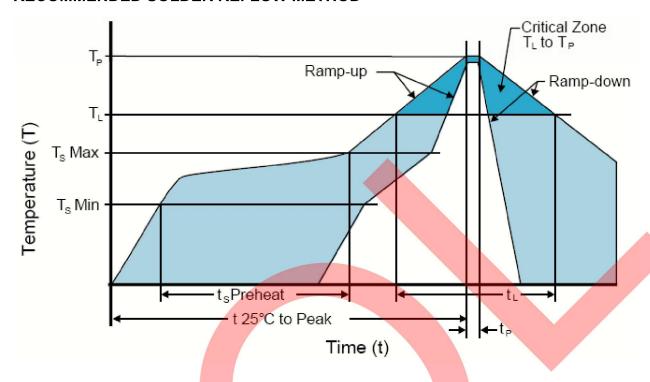
HIGH TEMPERATURE INFRARED/CONVECTION		
T _s MAX to T _L (Ramp-up Rate)	3°C/Second Maximum	
Preheat		
- Temperature Minimum (T _s MIN)	150°C	
- Temperature Typical (T _s TYP)	175°C	
- reinperature waxiiiuiii(15 wax)	200°C	
- Time (t _s MIN)	60 - 180 Seconds	
Ramp-up Rate (T _L to T _P)	3°C/Second Maximum	
Time Maintained Above:		
i diliporaturo (11)	217°C	
- Time (t _L)	60 - 150 Seconds	
Peak Temperature (T _P)	260°C Maxim <mark>um for 10</mark> Seconds Maximum	
Target Peak Temperature(T _P Target)	250°C +0 <mark>/-5°C</mark>	
Time within 5°C of actual peak (t _p)	20 - 40 Seconds	
Ramp-down Rate	6°C/Second Maximum	
Time 25°C to Peak Temperature (t)	8 Minutes Maximum	
Moisture Sensitivity Level	Level 1	
Additional Notes	Temperatures shown are applied to body of device.	

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device,)



RECOMMENDED SOLDER REFLOW METHOD



LOW TEMPERATURE INFRARED/CONVECTION		
T _s MAX to T _L (Ramp-up Rate)	5°C/Second Maximum	
Preheat		
- Temperature Minimum (T _s MIN)	N/A	
- Temperature Typical (T _s TYP)	150°C	
- reinperature waxiiiluin(1s wax)	N/A	
- Time (t _s MIN)	60 - 120 Seconds	
Ramp-up Rate (T _L to T _P)	5°C/Second Maximum	
Time Maintained Above:	¥	
- Temperature (T _L)	150°C	
- Time (t _L)	200 Seconds Maximum	
Peak Temperature (T _P)	240°C Maximum	
Target Peak Temperature(TP Target)	240°C M <mark>aximum 2</mark> Times/230°C Maximum 1Time	
Time within 5°C of actual peak (tp)	10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time	
Ramp-down Rate	5°C/Second Maximum	
Time 25°C to Peak Temperature (t)	N/A	
Moisture Sensitivity Level	Level 1	
Additional Notes	Temperatures shown are applied to body of device.	

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)